Department of Electrical and Computer Engineering The University of Texas at Austin

EE 460N, Spring 2012 Mattan Erez, Instructor Exam 1, February 27, 2012

Your signature is your promise that you have not cheated and will not cheat on this exam, nor will you help others to cheat on this exam.

Signature :	SOLUTION		
Printed Name ·			

Question:	1	2	Total
Points:	55	45	100
Score:			

Note: Please be sure that your answers to all questions (and all supporting work that is required) are contained in the space (boxes) provided. Anything outside the boxes will be ignored in grading. Use the back of each page as scratch paper, if needed.

Note: "I DON'T KNOW" is a valid answer that automatically gives you 10% of the maximum possible grade for that problem. Be sure to either erase, or cross-out everything else and write I DON'T KNOW in large, capital letters. Anything else will result in us grading what you have. A blank answer does not get you the 10%.

Note: Please put your name at the top of each page of the exam and remember that anything outside a box will be ignored!

Note: For all questions, unless otherwise stated, find the most efficient (time, resources) solution.

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1. Memory and buses.

This question had a couple of issues that made it less than ideal. If you are looking at this as a practice exam, please note that there are more ranks than I had intended and that the address pattern was meant to be sequential (0, 2, 4, 6, ...).

You have an LC3b processor with the memory configuration shown below. The program you care about most, accesses memory with LDW instructions and the access pattern is to sequential memory addresses (e.g. (in bytes): 0, 2, 4, 8, ...).

Memory capacity:	$64 \mathrm{KB}$	Row activate:	5 bus cycles
Channel width:	16b	Row precharge:	4 bus cycles
Bus frequency:	$1\mathrm{GHz}$	Column command:	1 bus cycle
Burst length:	1 bus beat	Number of ranks per DIMM:	4
Chip interface width:	8	Number of DIMMs per channel:	2
Number of channels:	2	Columns per row:	32
Number of banks per chip:	4		

(a) (5 points) Should the bus use pending or split transactions? Why?

Split -- allows row commands to be sent while waiting for previous column commands to complete.

(b) (10 points) Fill in the table below describing more memory characteristics.

Ranks per channel	8
Total DRAM chips	32
Capacity per bank	512B
Rows per bank	16

(c) (13 points) How would you interleave the different components of the DRAM organization to maximize throughput? Show your answer by associating bits of the address with organization components. The example below is *incorrect and incomplete*, but shows what we mean by associating bits with components.

15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	rank		chai	nnel		col				row				bank	

15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	Ro	W.				Col				Ra	nk/b	ank		Ch	X

If interpreted as 0,2,4,8 then only 0 bit mattered + channel not in bit 1-9

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(d) (7 points) What would be the throughput (in GB/s) assuming the described access pattern, your interleaving, and a memory controller that issues memory operations in order and does not overlap row and column commands. Assume that the processor is not the bottleneck and can generate requests as fast as memory can handle them – memory or the memory channels will bound the throughput. State any additional assumptions you make.

```
Just under 2GB/s for sequential .24GB/s for 0,2,4,8
```

(e) (13 points) You are now told that you must use a new type of DRAM chip. In this DRAM chip every column command is automatically precharges the bank (removes the row from the row buffer and writes it back to the array). How would you now interleave the different components of the DRAM organization to maximize throughput?

```
      15 | 14 | 13 | 12 | 11 | 10 | 9 | 8 | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0

      Unintentionally, same as Part C
```

(f) (7 points) What would be the throughput (in GB/s) be now with your new interleaving?

```
2GB/s for sequential .24GB/s for 0,2,4,8
```

Name:	

- 2. ISA, Microcode, and Microarchitecture
 - (a) (3 points) What is the key advantage of the architecture-microarchitecture separation (20 words or fewer)? We accepted anything reasonable. Examples below.

Enables software and hardware to evolve independently.

(b) (3 points) What is an alternative to a microcoded microarchitecture (20 words or fewer)?

One alternative is dedicated hardware resources for each ISA instruction.

(c) (2 points) What is a major advantage of choosing a microcoded microarchitecture (20 words or fewer)?

One major advantage is that it is very efficient in terms of number of gates needed for implementation.

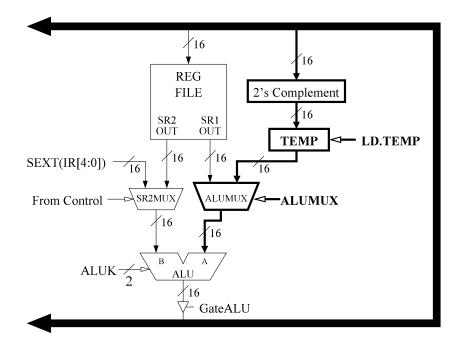
(d) (2 points) What is a major disadvantage of choosing a microcoded microarchitecture (20 words or fewer)?

One disadvantage is potentially slower operation (many micro-ops per ISA instruction.

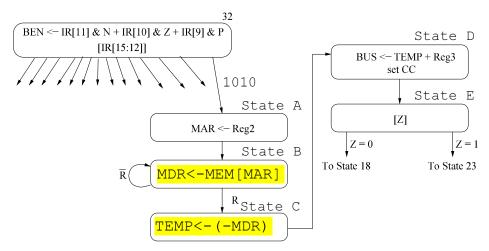
Now, consider adding the following new instruction to the LC3b. Your goal is to use the clues provided to determine the functionality of the instruction, as well as complete its implementation.

15	12	11	9,	8	6	5	3	2	0	
1010							!			l
1010		Regi		Reg2		000)	Re	eg3	l

To accomplish this, we will need a small addition to the data path, shown below in boldface:



(e) (23 points) Some of the new microcode states, changes to existing microcode states are shown below and the control signal table is shown on the next page. Note that these are incomplete, but you have enough information to complete them. Please do so (on both pages, don't leave any empty boxes in either the table or state diagram).



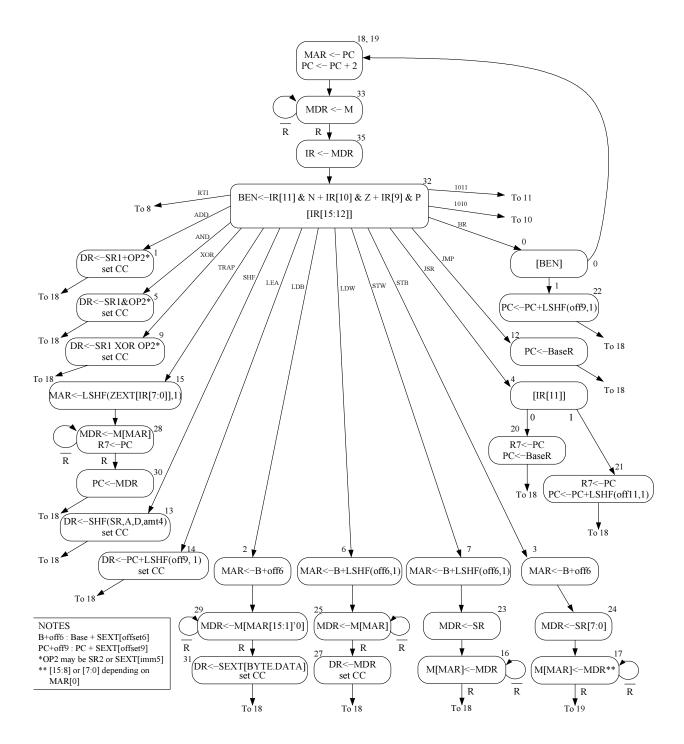
State 23 is described in bottom right of the LC3b state machine included on Page 7. Also, remember that putting data on the bus is fine provided there is only one writer.

	LD.PC	LD.MAR	LD.MDR	LD.CC	LD.TEMP	GatePC	GateMDR	GateALU	SR1MUX[1]	SR1MUX[0]	ALUMUX	ALUK[1]	ALUK[0]	MIO.EN	R.W
State A	0	1	0	0	0	0	0	1	0	1	1	1	1	0	X
State B	0	0	1	0	0	0	0	0	X	X	X	X	X	1	0
State C	0	0	0	0	1	0	1	0	X	X	X	X	X	0	X
State A	0	0	0	1	0	0	0	1	X	X	0	0	0	0	X
State E	0	0	0	0	0	0	0	0	X	X	X	X	X	0	X

LD.MDR	0: load not enabled1: load enabled	ALUK	00: ADD
LD.CC	0: load not enabled 1: load enabled		10: NOT 11: Pass input A
LD.TEMP	<pre>0: load not enabled 1: load enabled</pre>	MIO.EN	0: MIO not enabled 1: MIO enabled
GatePC	0: do not pass signal 1: pass signal	R.W	0: Read 1: Write
GateMDR	0: do not pass signal 1: pass signal	ALUMUX	0: TEMP 1: SR1OUT
GateALU	0: do not pass signal 1: pass signal		1. 581001

(f) (12 points) What does this new instruction do (20 words or fewer)?

If MEM[Reg2] equals content of Reg3 then CC set to Z and content of Reg1 is stored to MEM[Reg2]. Otherwise, CC set to N or P and memory remains unchanged.



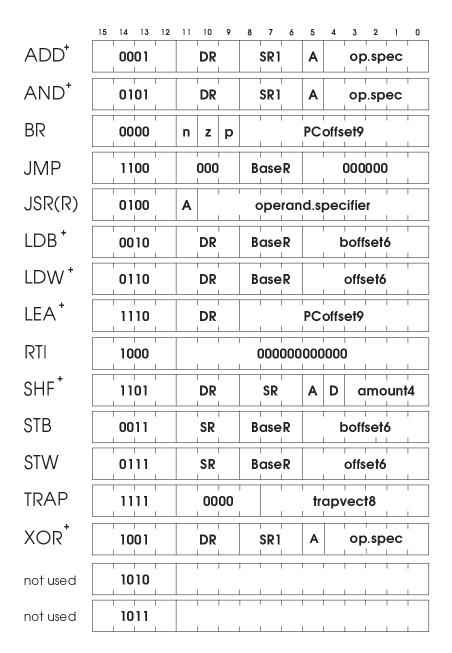


Figure A.2: Format of the instructions for the 16 LC-3b opcodes. NOTE: + indicates instructions that modify condition codes.